

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete If Known	
Sheet	1	of	1	Application Number	10/718,892
				Filing Date	11/21/03
				First Named Inventor	Dharmesh Jawarani et al.
				Group Art Unit	2813
				Examiner Name	Heather Doty
				Attorney Docket Number	SC13038TP

NON PATENT LITERATURE DOCUMENTS		
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
HJ	AA	OHGURO et al., "Nitrogen-doped Nickel Monosilicide Technique for Deep Submicron CMOS Salicide," IEEE 1995, pp. 453-456.

Examiner Signature	Heather Dwyer	Date Considered	4/19/05
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶Applicant is to place a check mark here if English Language Translation is attached.

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